TOSHIBA Intelligent Power Module Silicon N Channel IGBT

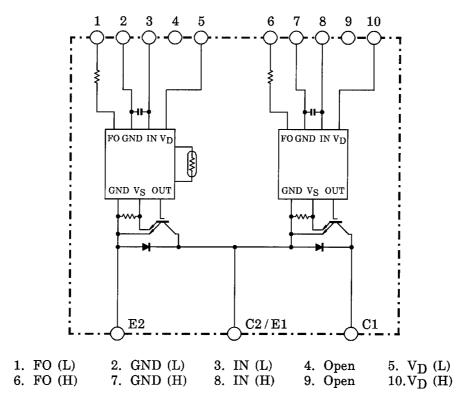
MIG200Q101H

High Power Switching Applications

Motor Control Applications

- Integrates inverter power circuits & control circuits (IGBT drive units, protection units for over-current, under-voltage & over-temperature) in one package.
- The electrodes are isolated from case.
- High speed type IGBT : V_{CE} (sat) = 3.5V (Max.)
 - t_{off} = 3.8µs (Max.)
 - t_{rr} = 0.24µs (Max.)
- Outline : TOSHIBA 2–121A1A
- Weight : 510g

Equivalent Circuit



Maximum Ratings (T_j = 25°C)

Stage	Characteristic	Condition	Symbol	Ratings	Unit
Inverter	Supply voltage	P-N power terminal	V _{CC}	900	V
	Collector-emitter voltage	_	V _{CES}	1200	V
	Collector current	Tc = 25°C, DC	Ι _C	200	А
	Forward current	Tc = 25°C, DC	IF	200	А
	Collector power dissipation	Tc = 25°C	PC	1600	W
	Junction temperature	_	Тј	150	°C
Control	Control supply voltage	V _D -GND terminal	VD	20	V
	Input voltage	IN-GND terminal	V _{IN}	20	V
	Fault output voltage	FO-GND (L) terminal	V _{FO}	20	V
	Fault output current	FO sink current	I _{FO}	14	mA
Module	Operating temperature	_	т _с	-20~+100	°C
	Storage temperature range	_	T _{stg}	-40~+125	°C
	Isolation voltage	AC 1 minute	V _{ISO}	2500	V
	Screw torque	M6	—	3	Nm

Electrical Characteristics (T_j = 25°C)

a. Inverter stage

Characteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Collector cut-off current	I _{CEX} V _{CEX} = 1200V	1/2 = 1200	T _j = 25°C	_	—	2	mA
		T _j = 125°C	_	_	40		
Collector-omitter acturation voltage	V _{CE (sat)}	V _D = 15V, I _C = 200A V _{IN} = 3V→0V	T _j = 25°C	_	2.7	3.5	V
Collector-emitter saturation voltage			T _j = 125°C	_	2.6	_	
Forward voltage	VF	I _F = 200A		_	2.0	2.7	V
	t _{on}	V _{CC} = 600V, I _C = 200A V _D = 15V, V _{IN} = 3V↔0V Inductive load		0.8	1.5	2.2	μs
	t _{c (on)}			_	0.5	1.0	
Switching time	t _{rr}			_	0.16	0.24	
	t _{off}]	(Note 1)	_	3.3	3.8	
	t _{c (off)}			_	0.4	0.8	

b. Control Stage (T_j = 25°C)

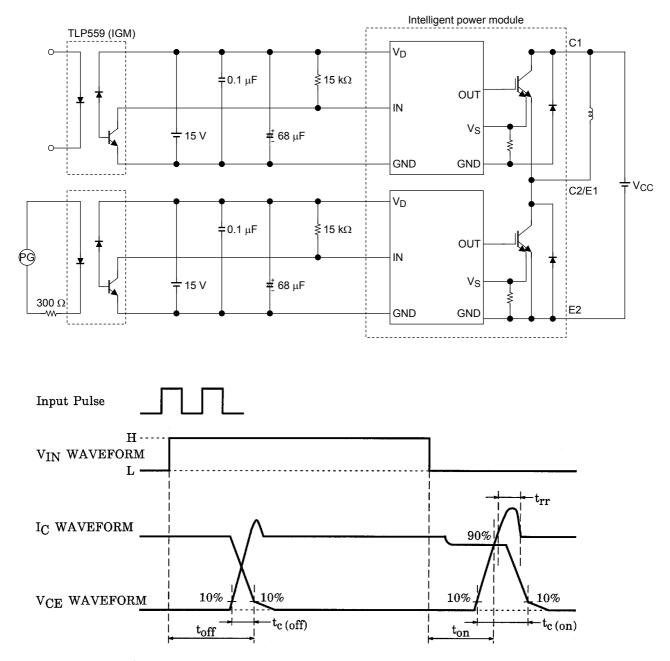
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Control circuit current		I _D	V _D = 15V	—	20	30	mA
Input on signal voltage		V _{IN (on)}	V _D = 15V, I _C = 200mA	0.9	1.1	1.3	V
Fault output current	Protection	I _{FO (on)}	– V _D = 15V	8	10	12	mA
	Normal	I _{FO (off)}		_	_	1	
Over current protection trip level		OC	V _D = 15V, T _j = 125°C	280	400	_	А
Short circuit protection trip level		SC	V _D = 15V, T _j = 125°C	420	600	_	А
Over current cut-off time		t _{off (OC)}	V _D = 15V	_	10	_	μs
Over temperature	Trip level	ОТ	Case temperature	111	118	125	°C
protection	Reset level	OTr		93	100	107	
Control supply under	Trip level	UV		11.3	12.0	12.7	v
voltage protection	Reset level	UVr] –	11.8	12.5	13.2	v
Fault output pulse width		t _{FO}	V _D = 15V	1	2	3	ms

c. Thermal Resistance ($T_j = 25^{\circ}C$)

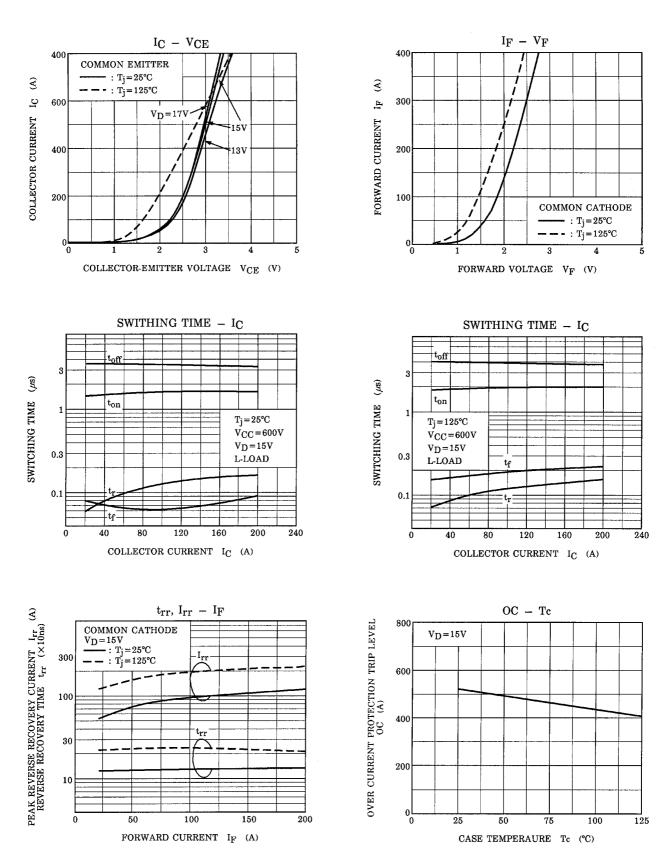
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Junction to case thermal resistance	D	IGBT	_	—	0.078	°C/W
Sunction to case thermal resistance	R _{th (j−c)}	RD — —	_	0.25	0,11	
Case to fin thermal resistance	R _{th (c−f)}	Compound is applied	_	0.05	_	°C/W

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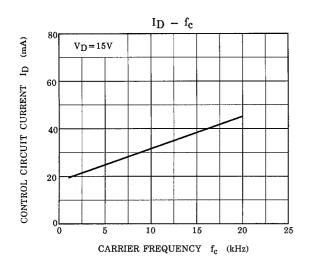
Note 1: Switching time test circuit & timing chart

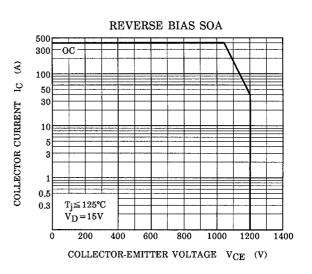


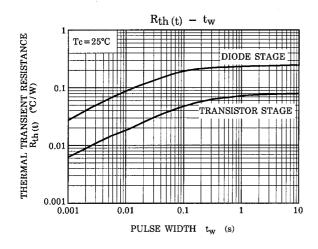
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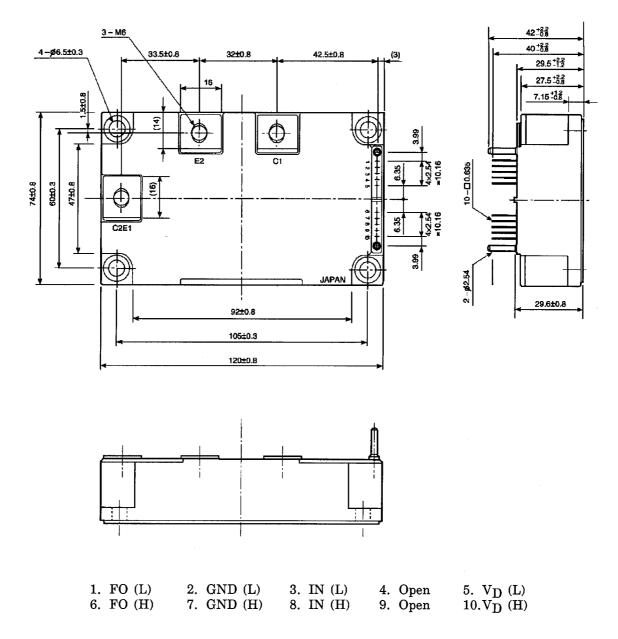




Package Dimensions

TOSHIBA 2-121A1A

Unit: mm



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